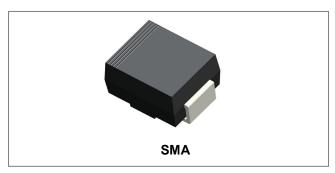






# 15MQ045N SCHOTTKY RECTIFIER



### **Features**

- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### **Circuit Diagram**



### **Applications**

- Disk Drives
- Switching power supply
- · Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

# **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	45	V
Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>L</sub> =105°C, rectangular wave form On PC board 9mm² island	2.1	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse, T <sub>C</sub> = 25 °C	60	А

### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 1 A, Pulse, T <sub>J</sub> = 25 °C	0.38	0.42	V
		@ 2 A, Pulse, T <sub>J</sub> = 25 °C	0.42	0.49	V
	$V_{F2}$	@ 1 A, Pulse, T <sub>J</sub> = 100 °C	-	0.34	V
		@ 2 A, Pulse, T <sub>J</sub> = 100 °C	-	0.43	V
Reverse Current*	I <sub>R1</sub>	$@V_R = Rated V_R, Pulse, T_J = 25 °C$	0.03	1.0	mA
	I <sub>R2</sub>	$@V_R = Rated V_R, Pulse, T_J = 125 °C$	-	20	mA
Junction Capacitance	Ст	$@V_R = 10V, T_C = 25 °C$ $f_{SIG} = 1MHz$	95	134	PF
Typical Series Inductance	Ls	Measured lead to lead 5 mm from package body	2.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

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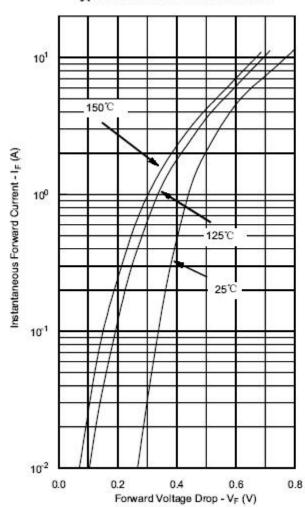


### **Thermal-Mechanical Specifications:**

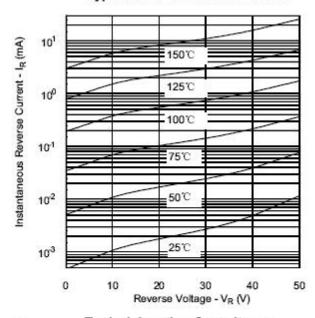
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Ambient	$R_{ heta JA}$	-	80	°C/W
Approximate Weight	wt	-	0.06	g
Case Style	SMA			

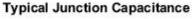
# **Ratings and Characteristics Curves**

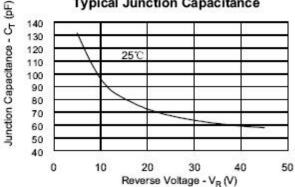
### **Typical Forward Characteristics**



### Typical Reverse Characteristics







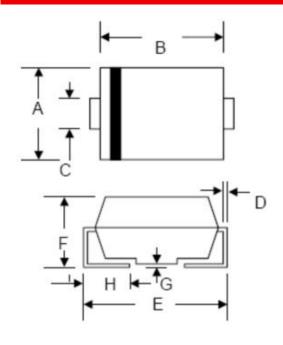
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### **Mechanical Dimensions SMA**



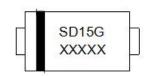
CVMDOL	Millimeters		Inches	
SYMBOL	Min.	Max.	Min.	Max.
Α	2.40	2.84	0.094	0.112
В	3.99	4.75	0.157	0.187
С	1.05	1.70	0.041	0.067
D	0.15	0.51	0.006	0.020
E	4.80	5.66	0.189	0.223
F	1.90	2.95	0.075	0.116
G	0.05	0.203	0.002	0.008
Н	0.76	1.52	0.030	0.600

### **Ordering Information**

Device	Package	Shipping	
15MQ045N	SMA (Pb-Free)	5000pcs / reel	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

### **Marking Diagram**



Where XXXXX is YYWWL

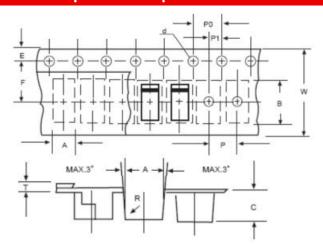
S = Device Type
D = Package Type
15 = Forward Current (1.5A)
G = Reverse Voltage (45V)

YY = Year WW = Week L = Lot Number

Cautions: Molding resin

Epoxv resin UL:94V-0

# **Carrier Tape & Reel Specification SMA**



SYMBOL	Millimeters		
STWIBUL	Min.	Max.	
Α	2.97	3.17	
В	5.70	5.90	
C	2.32	2.52	
d	1.40	1.60	
E	1.40	1.60	
F	5.60	5.70	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
Т	0.25	0.35	
W	11.80	12.20	

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